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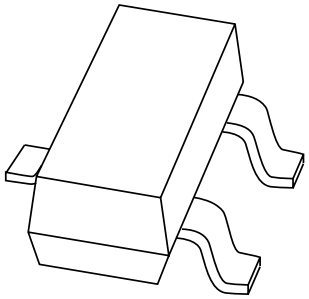
Kind regards,

Team Nexperia

DATA SHEET



BAS116
Low-leakage diode

Product data sheet
Supersedes data of 1999 May 26

2003 Dec 12

Low-leakage diode BAS116

FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATION

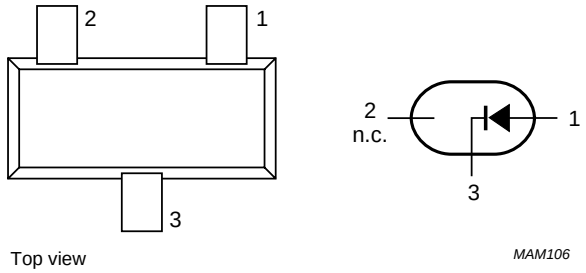
- Low leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial medium-speed switching diode with a low leakage current in a small SOT23 plastic SMD package.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



Marking code: JVt = made in Malaysia; JVp = made in Hong Kong; JVW = Made in China.

Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BAS116	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	see Fig.2; note 1	–	215	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t_p = 1 μs	–	4	A
		t_p = 1 ms	–	1	A
		t_p = 1 s	–	0.5	A
P_{tot}	total power dissipation	T_{amb} = 25 °C; note 1	–	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	forward voltage	see Fig.3			
		I_F = 1 mA	–	0.9	V
		I_F = 10 mA	–	1	V
		I_F = 50 mA	–	1.1	V
		I_F = 150 mA	–	1.25	V
I_R	reverse current	see Fig.5			
		V_R = 75 V	0.003	5	nA
		V_R = 75 V; T_j = 150 °C	3	80	nA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	2	–	pF
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	0.8	3	μs

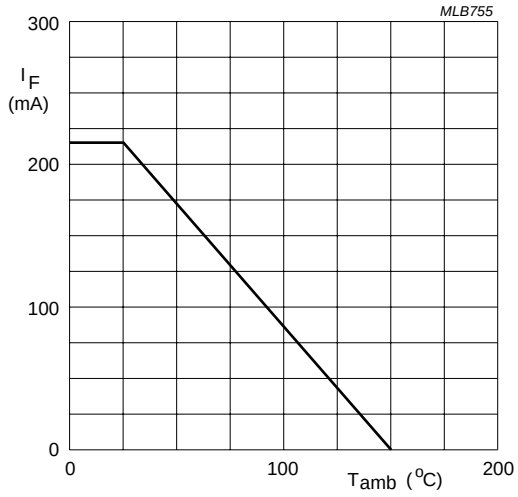
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j\text{-}tp)}$	thermal resistance from junction to tie-point		330	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

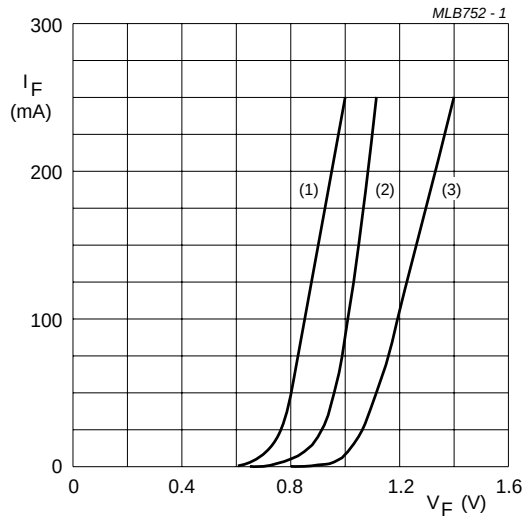
1. Device mounted on an FR4 printed-circuit board.

GRAPHICAL DATA



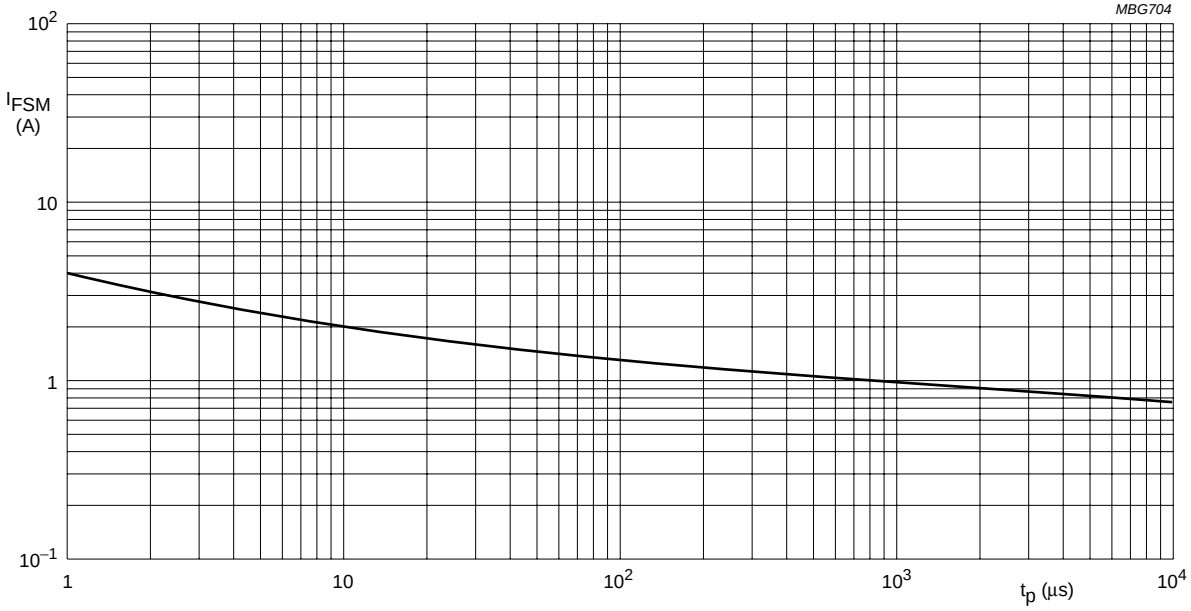
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



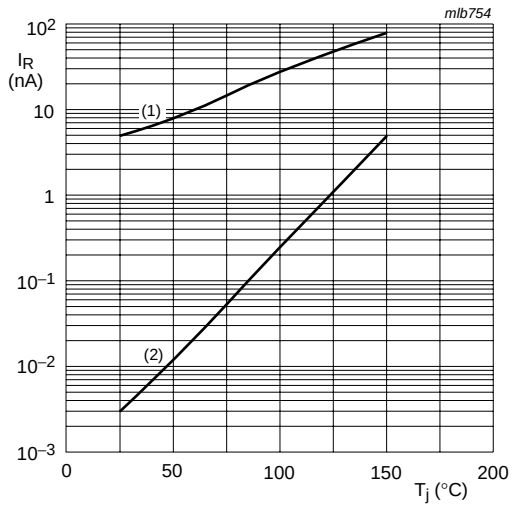
(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



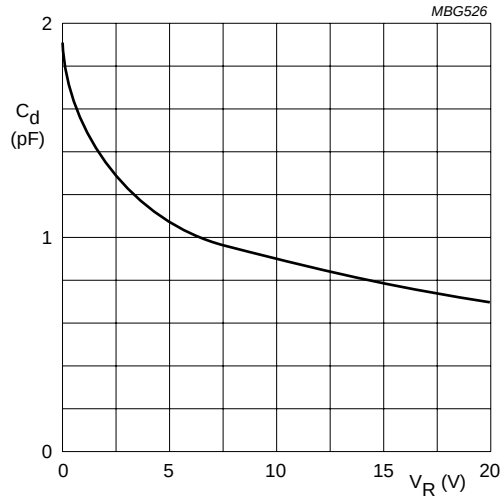
Based on square wave currents; T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.



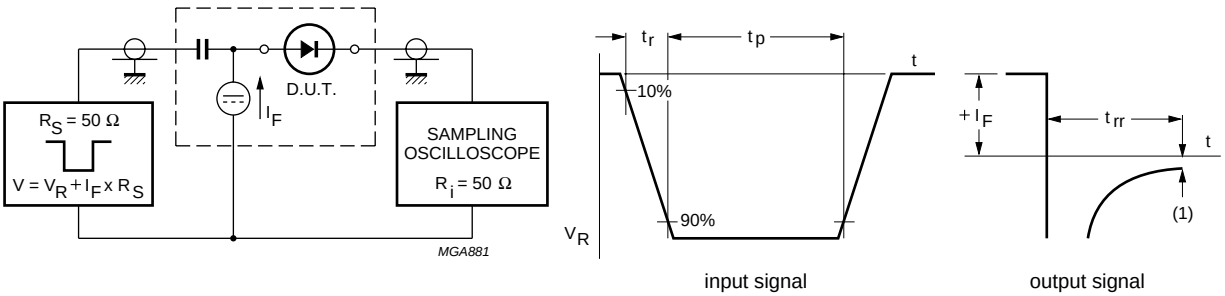
(1) Maximum values.
(2) Typical values.
V_R = 75 V.

Fig.5 Reverse current as a function of junction temperature.



f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

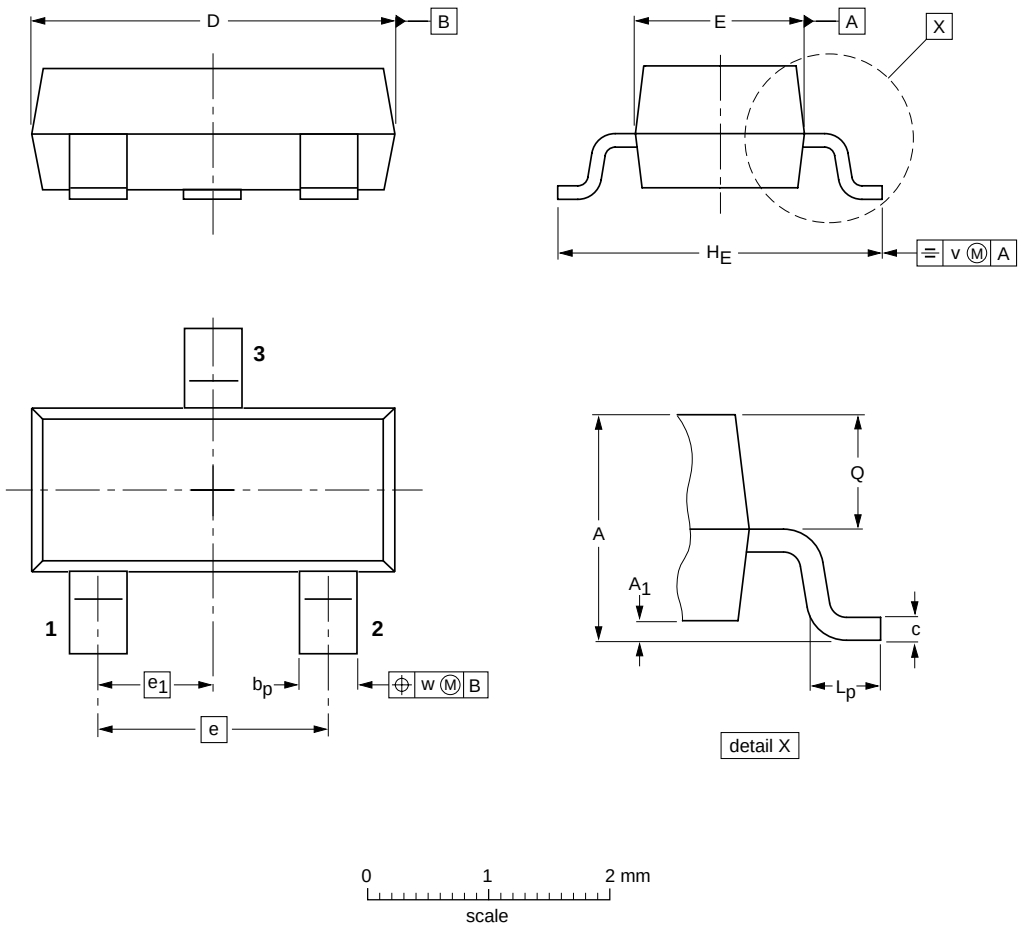


(1) I_R = 1 mA.

Fig.7 Reverse recovery time test circuit and waveforms.

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				~~04-11-04~~ 06-03-16

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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